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Substitute for form 1449A/PTO

**INFORMATION DISCLOSURE
STATEMENT BY APPLICANT**
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Sheet 1 of 12

Complete if Known

Application Number	Based on 10/214,691
Filing Date	August 9, 2002
First Named Inventor	Shunpei YAMAZAKI, et al.
Group Art Unit	2826
Examiner Name	Fetsum Abraham
Attorney Docket Number	0756-7218

10/7/2,062

U.S. PATENT DOCUMENTS

Examiner Initials ¹	Cite No. ¹	U.S. Patent Document		Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number	Kind Code ² (if known)			
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OTHER PRIOR ART – NON PATENT LITERATURE DOCUMENTS

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M		Japan J. Appl. Phys. 8 (1969) 1056, "Effect of Deposited Metals on the Crystallization Temperature of Amorphous Germanium Film," OKI et al.	
N		Technology Information Association, "Thermo-Auto-Chrome Full Color Recording Technology," May 31, 1995	

Examiner Signature	John Koral	Date Considered	01/23/03

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

¹ Unique citation designation number. ² See attached Kinds of U.S. Patent Documents. ³ Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). ⁴ For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. ⁵ Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST.16 if possible. ⁶ Applicant is to place a check mark here if English language Translation is attached.

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		JP	64-081324		03/27/89

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PR		IBM Technical Disclosure Bulletin, Vol. 11, No.7, A.R. Baker, Jr.			

Examiner Signature	<i>Fetsum Abraham</i>	Date Considered	2/8/05
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				Examiner Name	Fetsum Abraham
Sheet	3	of	12	Attorney Docket Number	0756-7218

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Examiner Signature	<i>John Koch</i>	Date Considered	2/8/05
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Sheet

4

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First Named Inventor	Shunpei YAMAZAKI, et al.
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Examiner Name	Fetsum Abraham
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Examiner Signature	<i>Fetsum Abraham</i>	Date Considered	<i>8/23/05</i>
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Examiner Signature	<i>Fetsum Abraham</i>	Date Considered	2/18/03
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Sheet	9	of	12	Application Number	Based on 10/214,691
				Filing Date	August 9, 2002
				First Named Inventor	Shunpei YAMAZAKI, et al.
				Group Art Unit	2826
				Examiner Name	Fetsum Abraham
				Attorney Docket Number	0756-7218

U.S. PATENT DOCUMENTS						
Examiner Initials ¹	Cite No. ¹	U.S. Patent Document		Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Page, Column, Lines, Where Relevant Passages or Relevant Figures Appear
		Number	Kind Code ² (if known)			
(P)		5,705,829		Miyanaga et al.	01/06/98	
		5,712,191		Nakajima et al.	01/27/98	
		5,756,364		Tanaka et al.	05/26/98	
		5,619,044		Makita et al.	04/08/97	
		5,530,266		Yonehara et al.	06/25/96	
		5,550,070		Funai et al.	08/27/96	
		5,693,959		Inoue et al.	12/02/97	

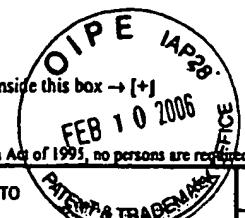
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NJZ		Kuznetsov et al., "Silicide Precipitate Formation and Solid Phase Re-Growth of Ni-Implanted Amorphous Silicon," April 5-8, 1993, pp. 191-194, Inst. Phys. Conf. Ser. No. 134.4: Proceedings of Royal Microscopical Society Conf.	
W		Liu et al., "Polycrystalline Silicon Thin Film Transistors on Corning 7059 Glass Substrates Using Short Time, Low-Temperature Processing," May 17, 1993, pp. 2554-2556, Appl. Phys. Lett 62(20)	
NJ		Liu et al., "Selective Area Crystallization of Amorphous Silicon Films by Low-Temperature Rapid Thermal Annealing," August 14, 1989, pp. 660-662, Appl. Phys. Lett 55(7)	
NJ		Spaepen et al., Metal-Enhanced Growth of Silicon, 1992, pp. 483-499, Crucial Issues in Semiconductor Materials & Processing Technologies	

Examiner Signature	<i>Fetsum Abraham</i>	Date Considered	<i>8/30/05</i>
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NJ

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Sheet 10 of 12

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Application Number	Based on 10/214,691
Filing Date	August 9, 2002
First Named Inventor	Shunpei YAMAZAKI, et al.
Group Art Unit	2826
Examiner Name	Fetsum Abraham

Attorney Docket Number

0756-7218

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		Number	Kind Code ² (If Known)			
	5,403,772			Zhang et al.	04/04/95	
	5,426,064			Zhang et al.	06/20/95	
	5,481,121			Zhang et al.	01/02/96	
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	5,492,843			Adachi et al.	02/20/96	
	5,501,989			Takayama et al.	03/26/96	
	5,508,533			Takemura	04/16/96	
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	5,543,352			Ohtani et al.	08/06/96	
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	5,620,910			Teramoto	04/15/97	
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	5,696,388			Funada et al.	12/09/97	
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				Examiner Name	Fetsum Abraham
				Attorney Docket Number	0756-7218

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		Number	Kind Code* (if known)		
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		5,535,471		07/16/96	
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		5,372,860		12/13/94	
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		5,893,730		04/13/99	
		5,913,111		06/15/99	
		5,953,597		09/14/99	
		6,011,275		01/04/00	
		6,133,073		10/17/00	

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PK		Wolf, <i>Silicon Processing for the VLSI Era</i> , Volume 2, Chapter 4, page 274 (1990).	

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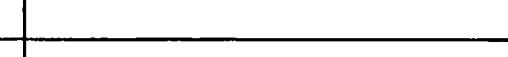
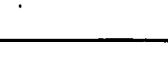
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				Filing Date	August 9, 2002
				First Named Inventor	Shunpei YAMAZAKI, et al.
				Group Art Unit	2826
				Examiner Name	Fetsum Abraham
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		Application Number	10/712,062
		Filing Date	November 14, 2003
		First Named Inventor	Shunpei YAMAZAKI et al.
		Group Art Unit	2826
		Examiner Name	Fetsum Abraham
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		Attorney Docket Number	0756-7218

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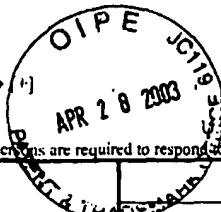
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NJH		Office Action dated August 3, 1998 for Application Serial No. 08/784,293.	
MEJ		Office Action dated February 11, 1999 for Application No. 08/784,293.	
MS		Office Action dated January 17, 2003 for Application No. 08/784,293.	
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				Examiner Name	F. Abraham
Sheet	1	of	1	Attorney Docket Number	0756-7026

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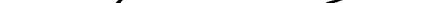
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	5,940,690			Kusumoto et al.	08/17/1999	
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